

General Description

The WSD30140DN56 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD30140DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

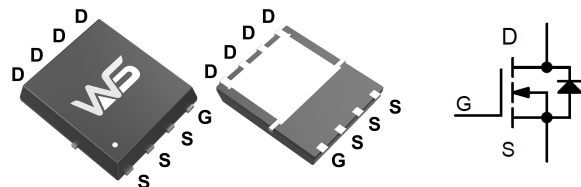
Product Summary

BVDSS	RDSON	ID
30V	1.7mΩ	85A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

DFN5X6-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,7}$	85	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,7}$	65	A
I_{DM}	Pulsed Drain Current ²	300	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	50	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	55	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.5	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.02	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	1.7	2.4	mΩ
		V _{GS} =4.5V, I _D =15A		2.5	3.3	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.7	2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	---	90	---	S
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =20A	---	26	---	nC
Q _{gs}	Gate-Source Charge		---	9.5	---	
Q _{gd}	Gate-Drain Charge		---	11.4	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GEN} =10V, R _G =3Ω, R _L =0.75Ω.	---	11	---	ns
T _r	Rise Time		---	6	---	
T _{d(off)}	Turn-Off Delay Time		---	38.5	---	
T _f	Fall Time		---	10	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	3000	---	pF
C _{oss}	Output Capacitance		---	1280	---	
C _{rss}	Reverse Transfer Capacitance		---	160	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	85	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =A, T _J =25°C	---	---	1.2	V

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t_s ≤ 10s junction to ambient thermal resistance rating.

Typical Characteristics

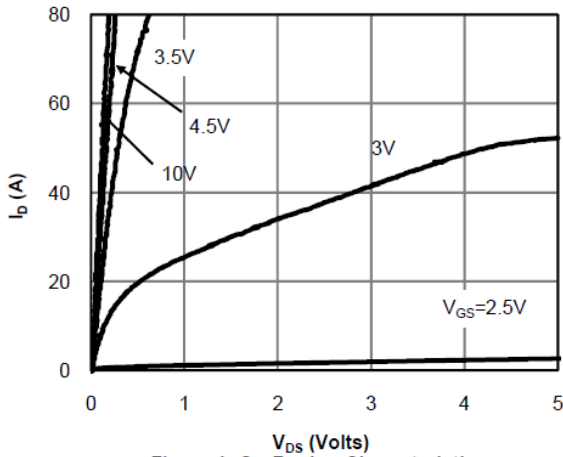


Figure 1: On-Region Characteristics

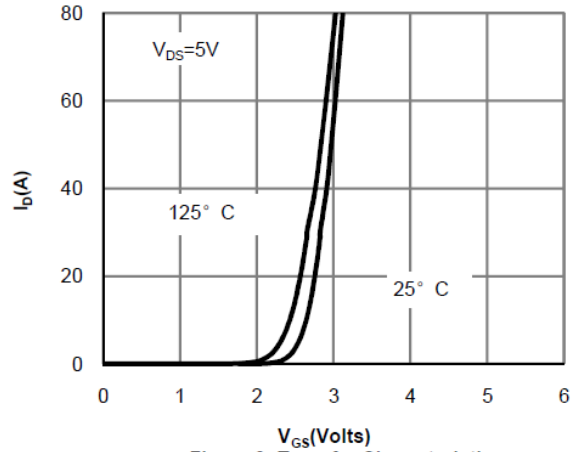


Figure 2: Transfer Characteristics

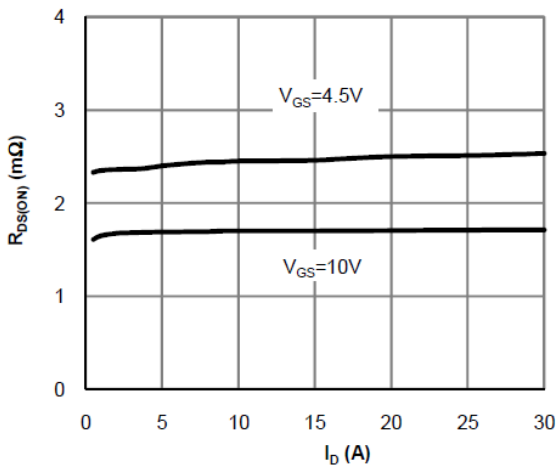


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

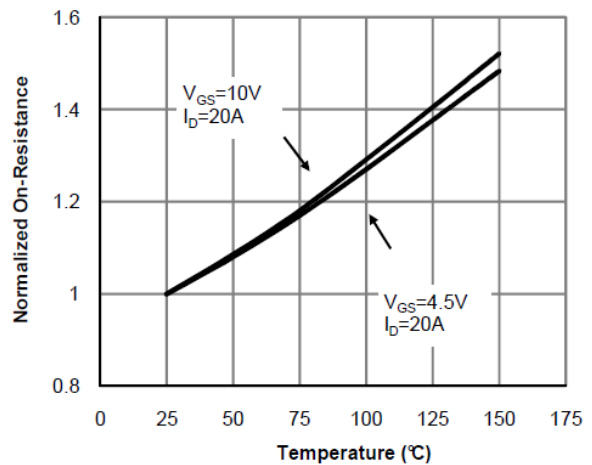


Figure 4: On-Resistance vs. Junction Temperature

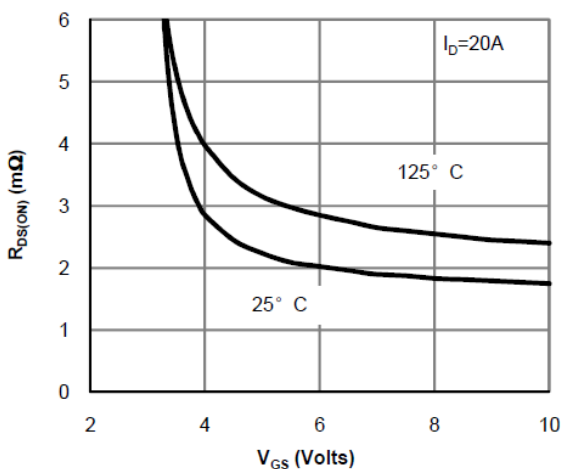


Figure 5: On-Resistance vs. Gate-Source Voltage

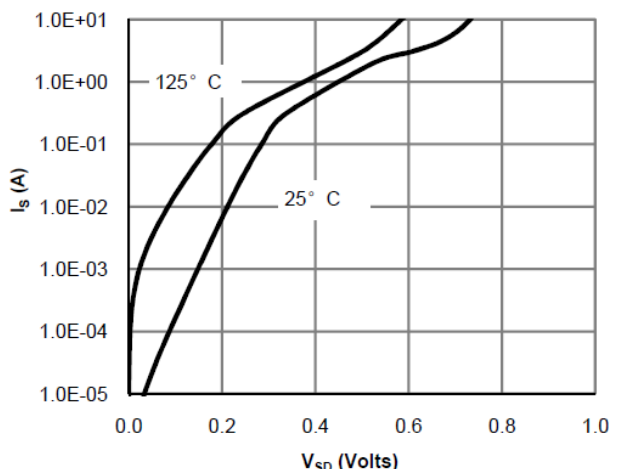


Figure 6: Body-Diode Characteristics

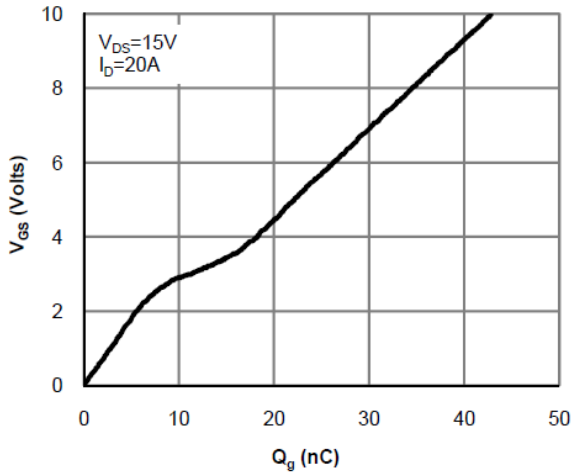


Figure 7: Gate-Charge Characteristics

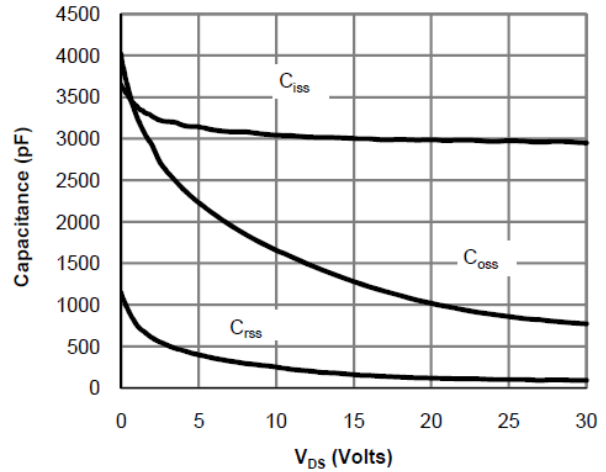


Figure 8: Capacitance Characteristics

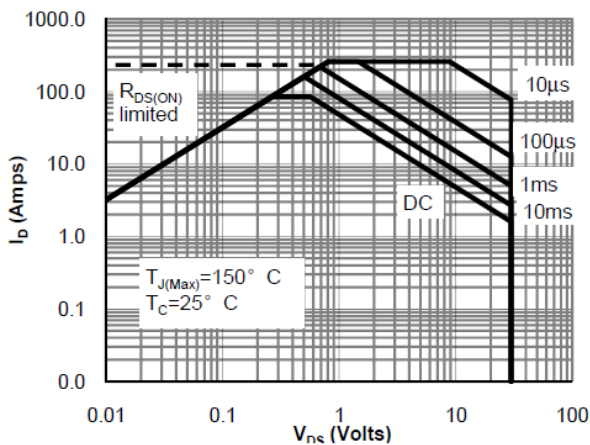


Figure 9: Maximum Forward Biased Safe Operating Area

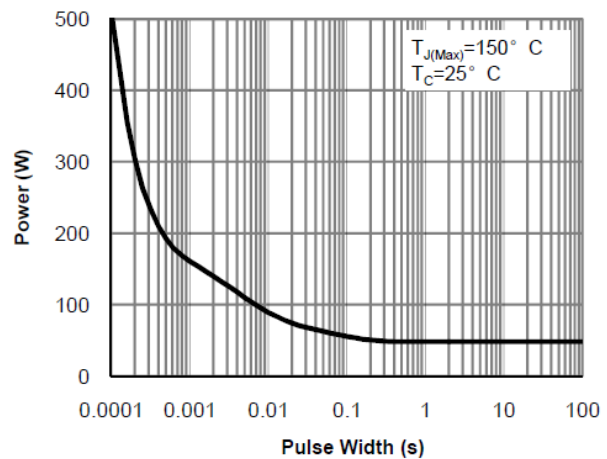


Figure 10: Single Pulse Power Rating Junction-to-Case

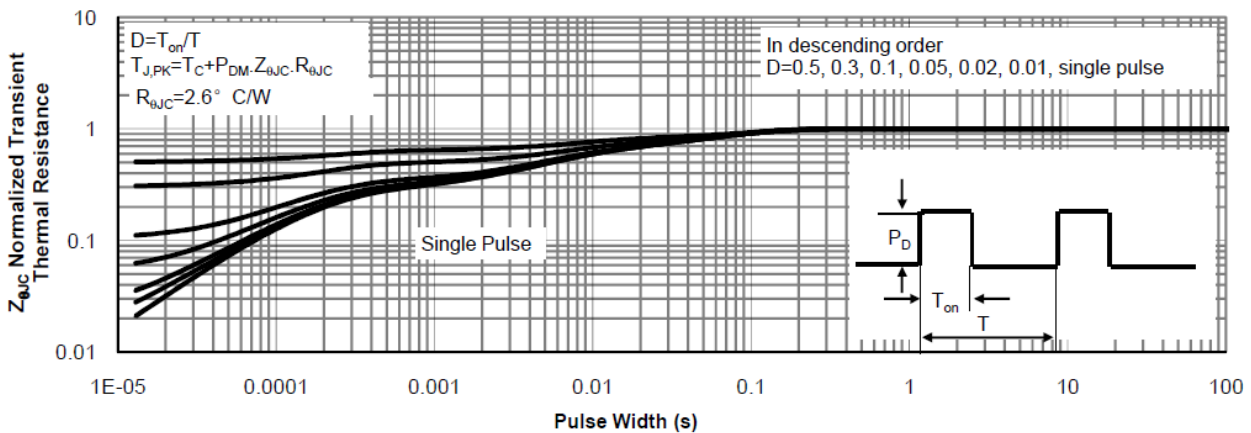


Figure 11: Normalized Maximum Transient Thermal Impedance



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